

TENTATIVE

TOSHIBA GATE TURN-OFF THYRISTOR LOW SNUBBER TYPE

SG2000GXH26

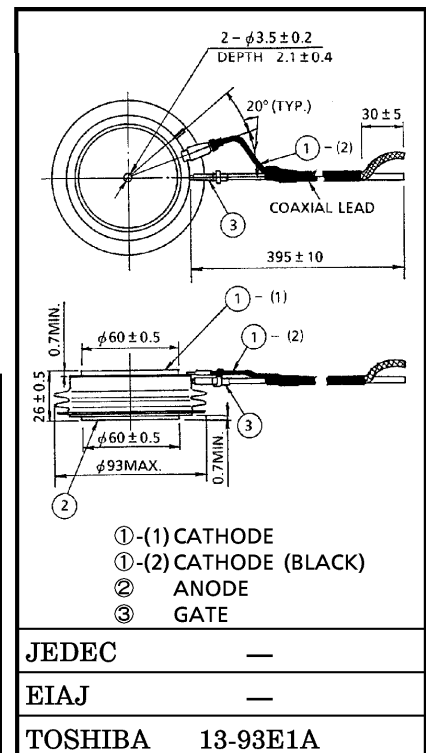
INVERTER APPLICATION

Unit in mm

- Repetitive Peak Off-State Voltage : $V_{DRM} = 4500 \text{ V}$ (Note 1)
- R.M.S On-State Current : $I_T(\text{RMS}) = 1000 \text{ A}$ ($T_f = 76^\circ\text{C}$)
- Peak Turn-Off Current : $I_{TGQM} = 2000 \text{ A}$
- Critical Rate of Rise of On-State Current : $di/dt = 500 \text{ A}/\mu\text{s}$
- Critical Rate of Rise of Off-State Voltage : $dv/dt = 1000 \text{ V}/\mu\text{s}$

MAXIMUM RATINGS

CHARACTERISTIC	SYMBOL	RATING	UNIT
Repetitive Peak Off-state Voltage (Note 1)	V_{DRM}	4500	V
Repetitive Peak Reverse Voltage	V_{RRM}	16	V
Peak Turn-Off Current (Note 2)	I_{TGQM}	2000	A
R.M.S On-State Current (Note 3)	$I_T(\text{RMS})$	1000	A
Peak One Cycle Surge On-State Current (non repetitive, 10 ms width half sine waveform)	I_{TSM}	16000	A
Critical Rate Of Rise Of On-State Current (Note 4)	di/dt	500	$\text{A}/\mu\text{s}$
Peak Forward Gate Current	I_{FGM}	100	A
Average Forward Gate Power Dissipation	$P_{FG}(\text{AV})$	50	W
Average Reverse Gate Power Dissipation	$P_{RG}(\text{AV})$	150	W
R.M.S Gate Current (Note 5)	$I_G(\text{RMS})$	42	A
Peak Reverse Gate Voltage (at Static)	V_{RGM}	16	V
Operating Junction Temperature Range	T_j	$-40 \sim 125$	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	$-40 \sim 150$	$^\circ\text{C}$
Mounting Force	—	19.6 ± 2.0	kN

(Note 1) : $V_{GK} = -2 \text{ V}$ (Note 2) : $V_{DM} = 4000 \text{ V}$, $C_S = 2 \mu\text{F}$, $R_S = 5 \Omega$, $di_{GQ}/dt = 35 \text{ A}/\mu\text{s}$, $V_{DSP} \leq 800 \text{ V}$,
 $L_S \leq 0.2 \mu\text{H}$ (Note 3) : 50 Hz Half Sine Waveform at $T_f = 76^\circ\text{C}$ (Note 4) : $V_D = 1/2 V_{DRM}$, $I_{GM} = 25 \text{ A}$ (Note 5) : Ambient Temperature of coaxial gate-cathode lead = 90°C 

Weight : 800 g

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ELECTRICAL CHARACTERISTICS

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN	TYP.	MAX	UNIT
Repetitive Peak Off-state Current	I_{DRM}	$V_{\text{DRM}} = \text{RATED}$, $V_{\text{GK}} = -2 \text{ V}$, $T_j = 125^\circ\text{C}$	—	—	100	mA
Repetitive Peak Reverse Current	I_{RRM}	$V_{\text{RRM}} = \text{RATED}$, $T_j = 125^\circ\text{C}$	—	—	10	mA
Repetitive Peak Reverse Gate Current	I_{RGM}	$V_{\text{RGM}} = 16 \text{ V}$, $T_j = 125^\circ\text{C}$	—	—	10	mA
Peak On-State Voltage	V_{TM}	$I_{\text{TM}} = 2000 \text{ A}$, $T_j = 125^\circ\text{C}$	—	—	3.60	V
Gate Trigger Voltage	V_{GT}	$V_{\text{D}} = 24 \text{ V}$, $R_{\text{L}} = 0.1 \Omega$	$T_j = -40^\circ\text{C}$	—	1.70	V
			$T_j = 25^\circ\text{C}$	—	1.20	V
Gate Trigger Current	I_{GT}		$T_j = -40^\circ\text{C}$	—	9.0	A
			$T_j = 25^\circ\text{C}$	—	3.0	A
Turn-On Delay Time	t_{d}	$V_{\text{D}} = 1/2 V_{\text{DRM}}$, $di/dt = 500 \text{ A}/\mu\text{s}$, $I_{\text{GM}} = 25 \text{ A}$, $I_{\text{T}} = 2000 \text{ A}$, $T_j = 25^\circ\text{C}$	—	—	3	μs
Turn-On Time	t_{gt}		—	—	10	μs
Critical Rate Of Rise Of Off-State Voltage	dv/dt	$V_{\text{DRM}} = 2/3 \text{ RATED}$, $T_j = 125^\circ\text{C}$, $V_{\text{GK}} = -2 \text{ V}$, Exponential Rise	1000	—	—	$\text{V}/\mu\text{s}$
Storage Time	t_{s}	$I_{\text{TGQ}} = 2000 \text{ A}$, $V_{\text{DM}} = 4000 \text{ V}$, $R_{\text{S}} = 5 \Omega$, $V_{\text{D}} = 1/2 V_{\text{DRM}}$, $di_{\text{GQ}}/dt = 35 \text{ A}/\mu\text{s}$, $C_{\text{S}} = 2 \mu\text{F}$, $V_{\text{DSP}} \leq 800 \text{ V}$, $T_j = 125^\circ\text{C}$, $L_{\text{S}} \leq 0.2 \mu\text{H}$	—	—	23	μs
Gate Turn-Off Time	t_{gq}		—	—	26	μs
Tail Time	t_{tail}		—	100	—	μs
Gate Turn-Off Current	I_{GQ}		—	520	—	A
Thermal Resistance (Junction to Fin)	$R_{\text{th(j-f)}}$	DC	—	—	0.018	$^\circ\text{C}/\text{W}$

